

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claims 1-10 (Canceled).

11. (Currently Amended) A method for manufacturing a semiconductor light emitting diode comprising the steps of:

(a) sequentially forming an n-type semiconductor layer, an active layer, and a p-type semiconductor layer on a substrate; and

(b) forming a p-type electrode on the p-type semiconductor layer, said p-type electrode being in electrical contact with the p-type semiconductor layer;

wherein step (b) includes sequentially forming a first metallic layer on the p-type semiconductor layer and a second metallic layer on the first metallic layer, said first metallic layer making ohmic contact with the p-type semiconductor layer, and ~~The method of claim 10, wherein step (b) further includes~~ thermally-processing the first and second metallic layers in a nonoxygen atmosphere at a temperature between 80°C and 260°C ~~350°C~~ inclusive and stabilizing the first and second metallic layers;

wherein the first metallic layer comprises a metal selected from the group consisting of palladium (Pd) and platinum (Pt), and the second metallic layer comprises silver (Ag) and is adapted to reflect light.

Claims 12-18 (Canceled).

19. (New) The method of claim 11, wherein the n-type semiconductor layer, the active layer, the p-type semiconductor layer are a GaN based III-IV nitride compound.

20. (New) The method of claim 11, wherein the active layer is an n-type or undoped $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$ ($0 \leq x \leq 1$, $0 \leq y \leq 1$, and $x+y \leq 1$) material layer.